2-Bit Translating Bus Switch

7WBD3306

The 7WBD3306 is an advanced high-speed low-power 2-bit translating bus switch in ultra-small footprints.

Features

- High Speed: $t_{PD} = 0.25 \text{ ns (Max)} @ V_{CC} = 4.5 \text{ V}$
- 3 Ω Switch Connection Between 2 Ports
- Power Down Protection Provided on Inputs
- Zero Bounce
- TTL-Compatible Control Inputs
- Ultra-Small Pb-Free Packages
- These are Pb-Free Devices-



ON Semiconductor®

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MARKING DIAGRAMS



UDFN8 MU SUFFIX CASE 517AJ





UDFN8 1.95 x 1.0 CASE 517CA





Micro8 DM SUFFIX CASE 846A





UQFN8 MU SUFFIX CASE 523AN





US8 US SUFFIX CASE 493





TSSOP8 DT SUFFIX CASE 948AL



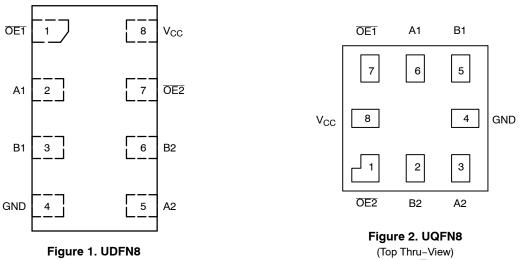
AH, X, D125, AF, AAE = Specific Device Code

M = Date Code
A = Assembly Location
L = Lot Code
Y = Year Code
W = Work Week Code
■ Pb-Free Package

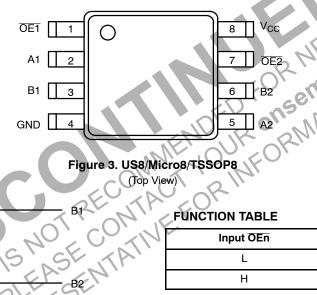
(Note: Microdot may be in either location)*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.



(Top Thru-View)



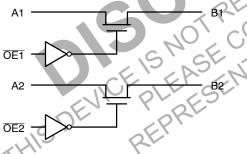


Figure 4. Logic Diagram

Input OEn	Function
L	Bn = An
Н	Disconnect

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	Control Pin Input Voltage	-0.5 to +7.0	V
V _{I/O}	Switch Input / Output Voltage	-0.5 to +7.0	V
I _{IK}	Control Pin DC Input Diode Current V _{IN} < GND	-50	mA
I _{OK}	Switch I/O Port DC Diode Current V _{I/O} < GND	-50	mA
I _O	ON-State Switch Current	± 128	mA
	Continuous Current Through V _{CC} or GND	± 150	mA
I _{CC}	DC Supply Current Per Supply Pin	± 150	mA
I _{GND}	DC Ground Current per Ground Pin	± 150	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	~N _° C
TJ	Junction Temperature Under Bias	150	⊘ `∘c
$ heta_{\sf JA}$	Thermal Resistance US8 (Note 1) UDFN8 UQFN8 Micro8 TSSOP8	251 111 208 392 150	°C/W
P _D	Power Dissipation in Still Air at 85°C US8 UDFN8 UQFN8 Micro8 TSSOP8	498 1127 601 319 833	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Mode (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
I _{LATCHUP}	Latchup Performance Above V _{CC} and Below GND at 125°C (Note 5)	±200	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.
- 2. Tested to EIA / JESD22-A114-A.
- 3. Tested to EIA / JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA / JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	Positive DC Supply Voltage		4.0	5.5	V
V _{IN}	Control Pin Input Voltage			5.5	V
V _{I/O}	Switch Input / Output Voltage			5.5	V
T _A	Operating Free-Air Temperature		-55	+125	°C
Δt / ΔV	Input Transition Rise or Fall Rate	Control Input Switch I/O	0 0	5 DC	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C		C	T _A -55°C to		
Symbol	Parameter	Conditions	(v)	Min	Тур	Max	Min	Max	Unit
V _{IK}	Clamp Diode Voltage	I _{I/O} = -18 mA	4.5			-1.2		-1.2	V
V _{IH}	High-Level Input Voltage (Control)		4.0 to 5.5	2.0			2.0		V
V _{IL}	Low-Level Input Voltage (Control)		4.0 to 5.5			0.8		0.8	V
V _{OH}	Output Voltage High	See Figure 5							
I _{IN}	Input Leakage Current	$0 \le V_{IN} \le 5.5 V$	5.5			±0.1		±1.0	μΑ
l _{OFF}	Power Off Leakage Current	V _{I/O} = 0 to 5.5 V	0			±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	$\begin{split} I_{O} &= 0, \\ V_{IN} &= V_{CC} \text{ or } 0 \text{ V} \\ \hline OE1 &= \overline{OE2} = GND \\ \overline{OE1} &= \overline{OE2} = V_{CC} \end{split}$	5.5			±1.0 ±0.1		±1.0 ±1.0	mΑ μΑ
Δl _{CC}	Increase in Supply Current (Control Pin)	One input at 3.4 V; Other inputs at V _{CC} or GND	5.5				VOE	2.5	mA
R _{ON}	Switch ON Resistance	$V_{I/O} = 0,$ $I_{I/O} = 64 \text{ mA}$ $I_{I/O} = 30 \text{ mA}$	4.5		3	7		7 7	Ω
		V _{I/O} = 2.4, I _{I/O} = 15 mA		CO	15	50	101	50	
		$V_{I/O} = 2.4,$ $I_{I/O} = 15 \text{ mA}$	4.0	IP	50	70		70	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS

		Vcc	T _A = 25 °C		T _A = -55°C to +125°C				
Symbol	Parameter S	Test Condition	(V)	Min	Тур	Max	Min	Max	Unit
t _{PD}	Propagation Delay, Bus to Bus	See Figure 6	4.0 to 5.5			0.25		0.25	ns
t _{EN}	Output Enable Time	See Figure 6	4.5 to 5.5	0.8	2.5	4.2	0.8	4.2	ns
<	YIO KI		4.0	0.8	3.0	4.6	0.8	4.6	
t _{DIS}	Output Disable Time		4.5 to 5.5	0.8	3.0	4.8	0.8	4.8	ns
			4.0	0.8	2.9	4.4	0.8	4.4	
C _{IN}	Control Input Capacitance	V _{IN} = 5 or 0 V	5.0		2.5				pF
C _{IO(ON)}	Switch On Capacitance	Switch ON	5.0		10				pF
C _{IO(OFF)}	Switch Off Capacitance	Switch OFF	5.0		5				pF

TYPICAL DC CHARACTERISTICS

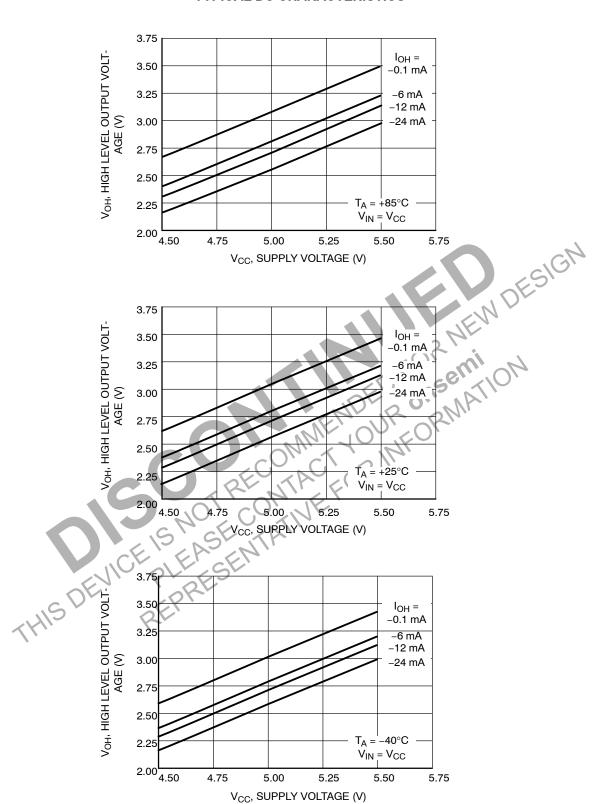
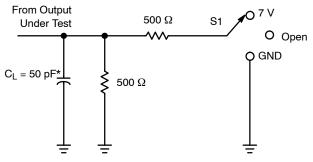


Figure 5. Output Voltage High vs Supply Voltage

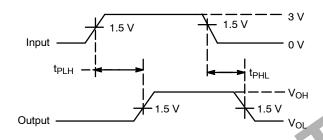
AC LOADING AND WAVEFORMS

Parameter Measurement Information

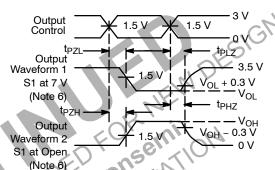


Test	S1
t _{PD}	Open
t _{PLZ} /t _{PZL}	7 V
t _{PHZ} /t _{PZH}	Open

^{*}CL includes probes and jig capacitance.



Voltage Waveforms Propagation Delay Times



Voltage Waveforms **Enable and Disable Times**

- Figure 6. t_{PD}, t_{EN}, t_{DIS} Loading and Waveforms 6. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \ \Omega$, $t_r \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- The outputs are measured one at a time, with one transition per measurement.
- 9. t_{PLZ} and t_{PHZ} are the same as t_{DIS} .
- 10.t_{PZL} and t_{PZH} are the same as t_{EN}.
- 11. t_{PHL} and t_{PLH} are the same as t_{PD}.

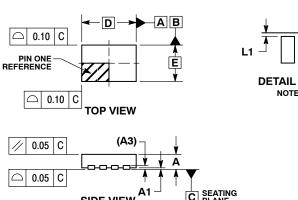
ORDERING INFORMATION

Device	Package	Shipping [†]
7WBD3306USG	US8 (Pb-Free)	3000 / Tape & Reel
7WBD3306MUTAG	UDFN8 (Pb-Free)	3000 / Tape & Reel
7WBD3306AMUTCG	UQFN8 (Pb-Free)	3000 / Tape & Reel
7WBD3306DMR2G	Micro8 (Pb-Free)	4000 / Tape & Reel
7WBD3306DTR2G	TSSOP8 (Pb-Free)	4000 / Tape & Reel
7WBD3306DMUTCG	UDFN8, 1.95 x 1.0, 0.5P (Pb-Free)	3000 / Tape & Reel

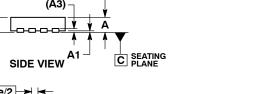
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

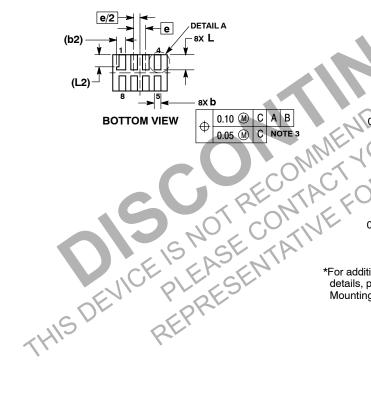
PACKAGE DIMENSIONS

UDFN8 1.8 x 1.2, 0.4P CASE 517AJ **ISSUE O**









NOTES:

- NOTES:

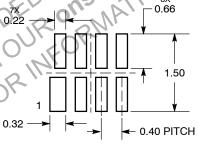
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSION 6 APPLIES TO PLATED TERMINAL AND 1S MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL TIP.
- MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS.
- 5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

	MILLIM	ETERS
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
A3	0.127	REF
b	0.15	0.25
b2	0.30	REF
D	1.80	BSC
E	1.20	BSC
е	0.40	BSC \
L	0.45	0.55
L1	0.00	0.03
Ľ2	0.40	RÉF

MOUNTING FOOTPRINT* SOLDERMASK DEFINED

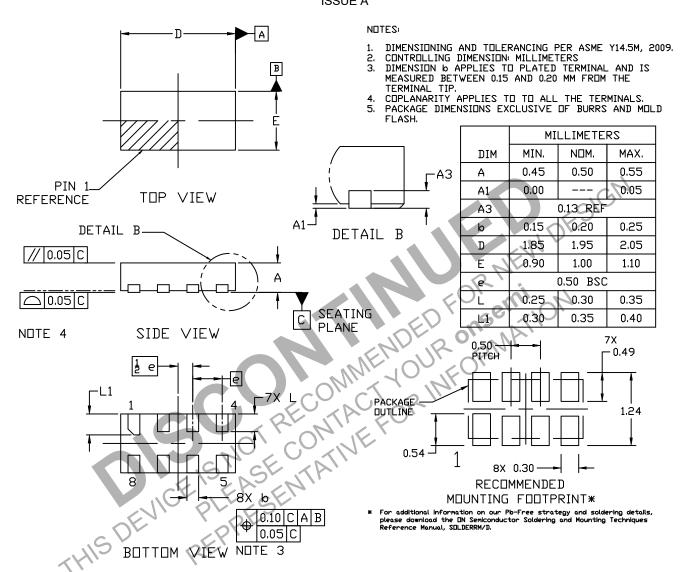


DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

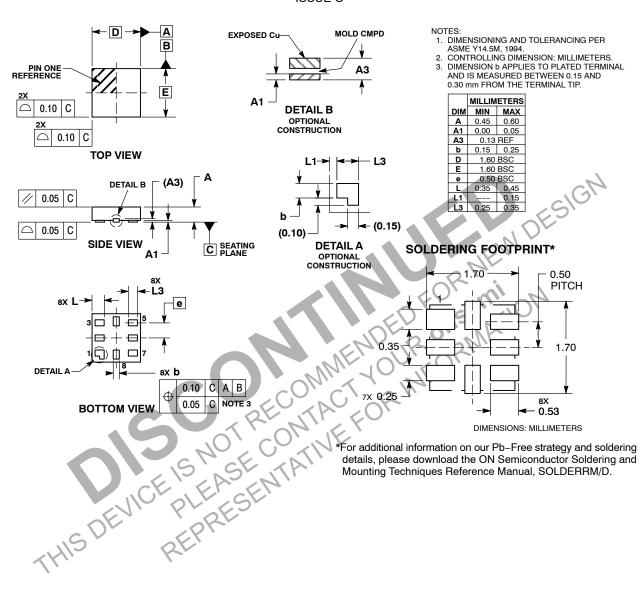
PACKAGE DIMENSIONS

UDFN8 1.95x1.0, 0.5P CASE 517CA ISSUE A



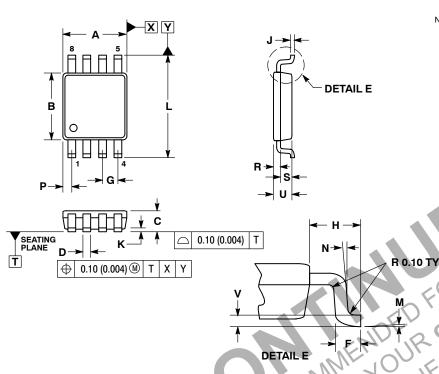
PACKAGE DIMENSIONS

UQFN8, 1.6x1.6, 0.5P CASE 523AN ISSUE O



PACKAGE DIMENSIONS

US8 **CASE 493** ISSUE D



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETERS.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.14MM (0.0055") PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH AND PROTRUSION SHALL NOT EXCEED 0.14MM (0.0055") PER SIDE.
- (0.0055") PER SIDE. LEAD FINISH IS SOLDER PLATING WITH
- THICKNESS OF 0.0076-0.0203MM (0.003-0.008").
 ALL TOLERANCE UNLESS OTHERWISE

SPECIFIED ±0.0508MM (0.0002").

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.90	2.10	0.075	0.083
В	2.20	2.40	0.087	0.094
Ç	0.60	0.90	0.024	0.035
D	0.17	0.25	0.007	0.010
F	0.20	0.35	0.008	0.014
G	0.50	BSC	0.020	BSC
H	0.40	REF	0.016	REF
J	0.10	0.18	0.004	0.007
K	0.00	0.10	0.000	0.004
7	3.00	3.20	0.118	0.128
M	0 %	6°	0°	6°
N	0 °	10 %	0 °	10 °
P (0.23	0.34	0.010	0.013
R	0.23	0.33	0.009	0.013
S	0.37	0.47	0.015	0.019
U	0.60	0.80	0.024	0.031
V	0.12	BSC	0.005	BSC

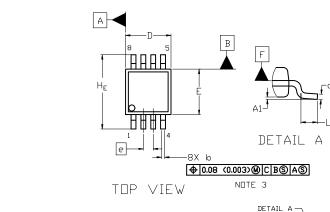
RECOMMENDED SOLDERING FOOTPRINT*

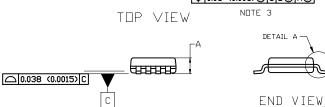


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

Micro8 CASE 846A ISSUE K

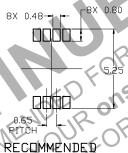




SIDE VIEW

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- 5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- 6. AT IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



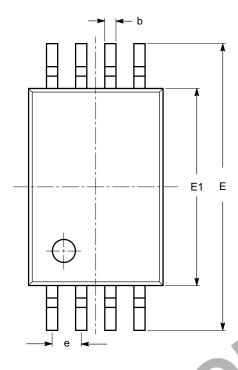
DIM	MILLIMETERS				
DIM	MIN.	N□M.	MAX.		
A	-	-	1.10		
∆ 1	0.05	0.08	0.15		
σ	0.25	0.33	0.40		
C	0.13	0.18	0.23		
D	2.90	3.00	3.10		
Е	2.90	3.00	3.10		
е	0.65 BSC				
HE	4.75	4.90	5.05		
L	0.40	0.55	0.70		

RECOMMENDED
MOUNTING FOOTPRINT

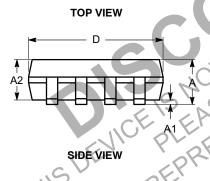
For additional information on due, Po-Free strategy or goldering lestals, piesse dependent the Dil Seniconducto SIL DERWIN Moseling Techniques Reference Normal.

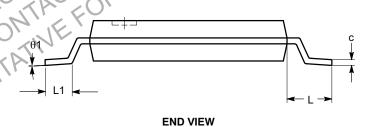
PACKAGE DIMENSIONS

TSSOP8, 4.4x3 CASE 948AL **ISSUE O**



SYMBOL	MIN	NOM	MAX		
Α			1.20		
A1	0.05		0.15		
A2	0.80	0.90	1.05		
b	0.19		0.30		
С	0.09		0.20		
D	2.90	3.00	3.10		
Е	6.30	6.40	6.50		
E1	4.30	4.40	4.50		
е		0.65 BSC			
L	1.00 REF				
Ì	0.50	0.60	0.75		
θ	0°	36, 41) 8⁰		





- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-153.

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